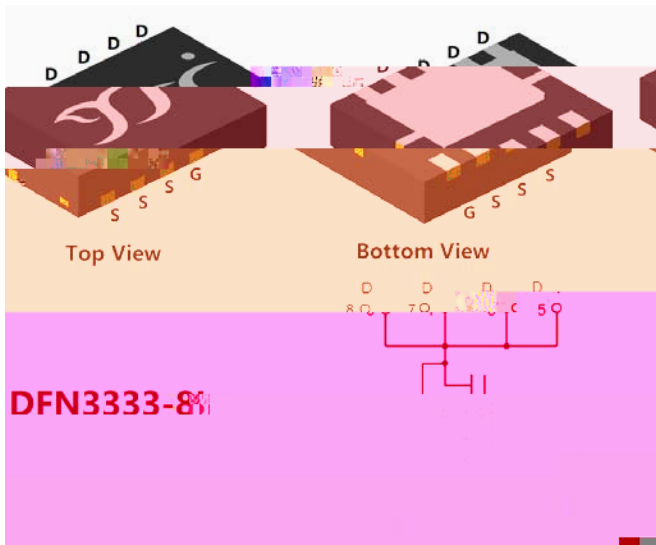




N-Channel Enhancement Mode Field Effect Transistor



Product Summary

• V_{DS}	60V
• I_D	18A
•	

■ Absolute Maximum Ratings (T

Drain Current	$T_C=25$	I_D	18	A
	$T_C=100$		11	
	$T_A=25$		5.7	
	$T_A=100$		3.6	
Pulsed Drain Current ^A		I_{DM}	60	A
Avalanche energy ^B		EAS	72	mJ

		θ_{JC}	6.7	/W
Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	60	/W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 +150	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJQ18N06AQ	F1	Q18N06A	5000	10000	100000	13" reel



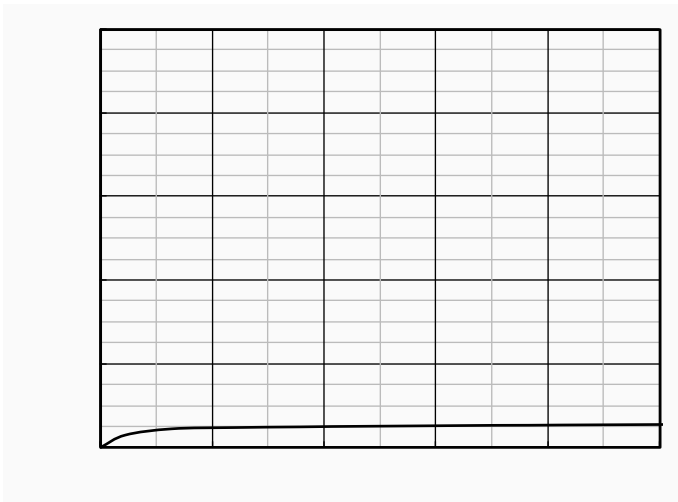
YJQ18N06AQ

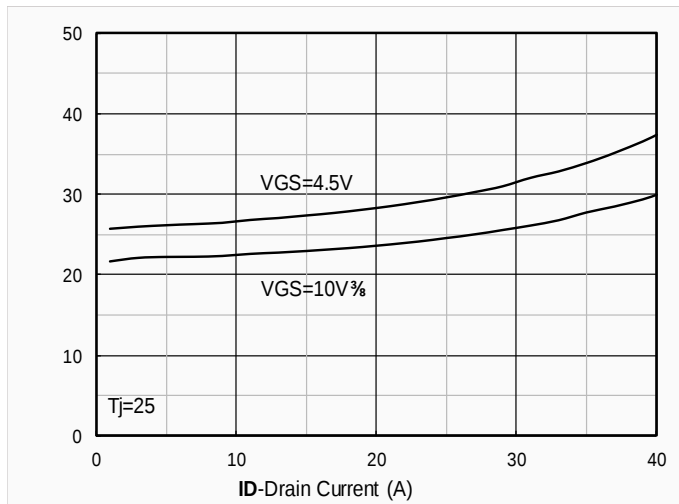
■ Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max
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■Typical Electrical and Thermal Characteristics Diagrams





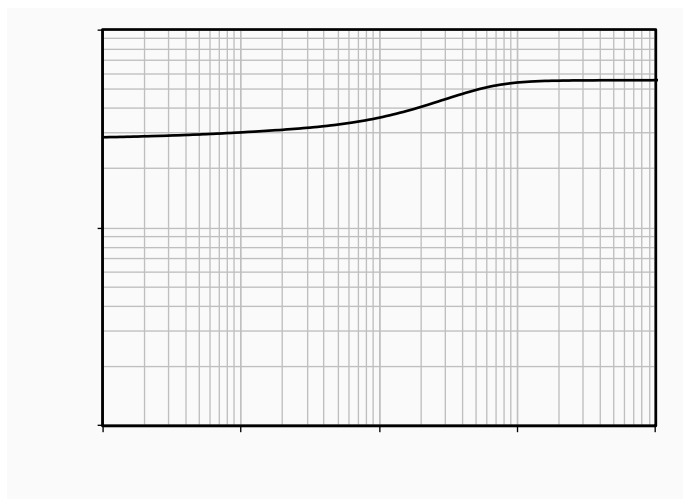


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area



■DFN3333-8L Package information

Note:

1.Controlling dimension:in millimeters.



Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herei



YJQ18N06AQ

Rev	Date	Modify content
1.0	30-Jun-23	New datasheet